



RECEIVED

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
FEB 21 2003

In re Application of

TC 2800 MAIL ROOM

USAMI, Tatsuya

Serial No.: 09/627,418

Group Art Unit: 2814

Filed: July 27, 2000

Examiner: Quach, T.

For: SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE  
SAME

Honorable Assistant Commissioner of Patents  
Washington, D.C. 20231

**AMENDMENT UNDER 37 C.F.R. §1.111**

Sir:

In response to the Office Action dated November 20, 2002, please amend the above-identified application as follows:

**IN THE CLAIMS:**

**Please amend claims 1 and 4, as follows:**

1. (Amended) A semiconductor device comprising:

a first interlayer insulating layer;

a plurality of wiring lines which are formed of Cu whose concentration is equal to or higher than  $10^{19}$  atoms/cm<sup>3</sup>, said plurality of wiring lines formed on said first interlayer insulating layer;

an insulating layer which has a property that Cu is unlikely to enter said insulating layer and which insulates between said plurality of wiring lines; and

a second interlayer insulating layer formed on said insulating layer having a property

that Cu is unlikely to enter therein.

RECEIVED  
FEB 21 2003  
TC 2800 MAIL ROOM

02/26/2003 DSA341 00000005 500481 09627418  
01 FC:1201 84.00 CH  
Adjustment date: 08/14/2003 SDIRETA  
02/26/2003 DSA341 00000005 500481 09627418  
01 FC:1201 84.00 CR